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(54) Oxide superconductor and method of manufacturing the same

(57) An oxide superconductor comprises a base material (11) consisting of a single crystalline oxide, an oxide superconductor film (2B) consisting of a Y123 compound and formed on the single crystalline oxide base material (11), and a coating film (3) consisting of

an oxide containing a Ba-Cu-O oxide as a main component and covering the surface of the oxide superconductor film (2B), the coating film (3) having a thermal expansion coefficient higher than that of the oxide superconductor film (2B)

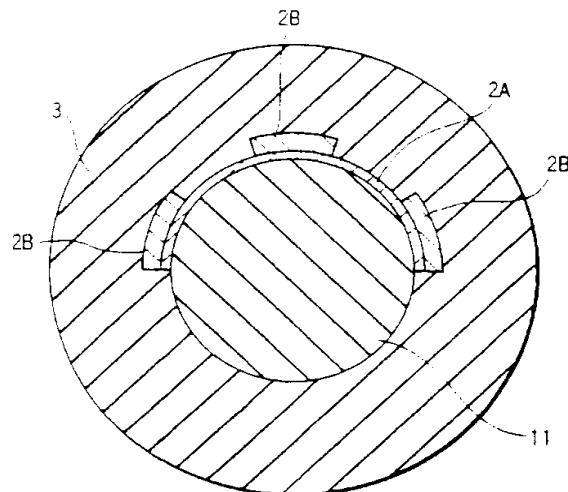


FIG. 2

Description

The present invention relates to an oxide superconductor and a method of manufacturing the same.

To allow an oxide superconductor to transport a large current the oxide superconductor is required to be highly oriented to exhibit an electromagnetic anisotropy and to be less in grain boundary acting as a weak link. To meet these requirements it was customary in the past to form an oxide superconductor film by vapor phase growth on an oriented oxide and/or metal substrate.

However, the deposition rate of the oxide superconductor film is considerably low in the vapor phase growing method, leading to a long time required for forming a film thick enough to transport a large current. In addition, the vapor phase growing method is known to bring about poor orientation and increased grain boundaries with increase in the thickness of the oxide superconductor film (Jpn. J. Appl. Phys. Vol. 31 (1992) pp. 2709-2715 and Supercond. Sci. Technol. 8 (1993) pp. 23-29; Printed in the UK). The vapor phase growing method is also known to give rise to cracks in the formed superconductor film, leading to breakage of the current path with increase in the thickness of the film.

A measure for solving the above-noted problems is proposed in, for example, Japanese Patent Disclosure (Kokai) No. 6-321694. Specifically, it is proposed to form an oxide superconductor film on a substrate by liquid phase epitaxy. This method certainly permits forming a relatively thick oxide superconductor film, which is less in grain boundary, in a short time. However, it is impossible to eliminate completely the cracks occurring in the oxide superconductor film, leaving room for further improvement in the critical current density of the oxide superconductor film.

An object of the present invention is to suppress the crack occurrence in an oxide superconductor film so as to improve the critical current density of the film.

According to an aspect of the present invention, there is provided an oxide superconductor comprising a base material consisting of a single crystalline oxide an oxide superconductor film formed on the oxide base material and a coating film covering the surface of the oxide superconductor film the coating film having a thermal expansion coefficient higher than that of the oxide superconductor film.

According to another aspect of the present invention there is provided a method of manufacturing an oxide superconductor comprising the steps of: forming an oxide superconductor film by a liquid phase growing method on a base material consisting of a single crystalline oxide and forming a coating film by a melt solidifying method to cover the surface of the oxide superconductor film.

In the present invention, an oxide superconductor film is covered with a coating film having a thermal expansion coefficient higher than that of the oxide super-

conductor film, with the result that the crack occurrence in the oxide superconductor film is suppressed. It follows that there exists less grain boundaries which act as weak links, leading to an improved critical current density of the superconductor film.

This invention can be more fully understood from the following detailed description when taken in conjunction with the accompanying drawings, in which

FIG. 1 is a cross sectional view showing the structure of an oxide superconductor obtained in Example 1.

FIG. 2 is a cross sectional view showing the structure of an oxide superconductor obtained in Example 2.

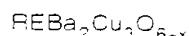
FIG. 3 is a graph showing the relationship between the magnetic field and critical current of an oxide superconductor obtained in Example 2, and

FIG. 4 is a graph showing the relationship between the temperature and resistance of an oxide superconductor of comparative example.

The present invention provides an oxide superconductor comprising a base material consisting of a single crystalline oxide, an oxide superconductor film formed on the oxide base material, and a coating film covering the surface of the oxide superconductor film.

In the present invention a single crystalline oxide such as yttria-stabilized zirconia (YSZ) or SrTiO_3 can be used as a base material. The shape of the base material is not particularly limited in the present invention that is the base material can be in the form of, for example a substrate or a fiber.

It is possible to use as an oxide superconductor a so-called "1-2-3 compound" represented by the general formula given below



where RE denotes at least one element selected from the group consisting of Y and rare earth elements and 0 \leq x \leq 1. A specific example of the 1-2-3 compound is $\text{YBa}_2\text{Cu}_3\text{O}_{6-x}$ hereinafter referred to as "Y123".

An oxide containing Ba-Cu-O as a main component can be used as a coating material. It should be noted that the Ba-Cu-O oxide has a thermal expansion coefficient higher than that of Y123 crystal.

The oxide superconductor of the present invention can be manufactured as follows. In the first step an oxide superconductor film, e.g., a Y123 film, is formed by a melt growing method on the surface of a single crystalline oxide base material. To be more specific, flux which consists of BaO, CuO and so on and a raw material of an oxide superconductor such as Y211 compound are melted in a crucible. In this step, a melt of the raw material of the oxide superconductor is present in

A bottom portion of the crucible and a melt containing mainly a Ba-Cu-O oxide is present in an upper portion of the crucible. Under this condition, the base material is brought into contact with the melt to permit the Y123 compound which is migrated through the melt to be deposited on the base material to form a Y123 film. When the Y123 film has grown to have a desired thickness the base material is moved away from the melt. In moving the base material away from the melt, the melt of the Ba-Cu-O based oxide is solidified to form a coating film. A homogeneous coating film can be obtained by controlling, for example, the temperature of the melt and the time required for moving the base material away from the melt. A homogeneous coating film can be formed in the case of using a fiber as a base material because the fiber has a relatively small diameter and a large surface area per unit volume and, thus, to a good cooling efficiency. Incidentally, formation of a coating film was not considered to be desirable in the past.

Where a coating film having a high thermal expansion coefficient is formed to cover the surface of an oxide superconductor film, e.g., Y123 film, as in the present invention, a compressive stress caused by shrinkage of the coating film acts on the oxide superconductor film so as to suppress crack occurrence in the oxide superconductor film.

Examples

Let us describe the present invention more in detail with reference to the accompanying drawings.

Example 1

FIG. 1 is a cross sectional view showing an oxide superconductor prepared in this Example. As shown in the drawing, an oxide superconductor film 2 consisting of a Y123 seed crystal 2A and a Y123 film 2B is formed on a substrate 1 consisting of a YSZ single crystal. Further, a coating film 3 consisting of an oxide containing a Ba-Cu-O oxide as a main component is formed to cover the upper surface of the oxide superconductor film 2. The coating film 3 has a thermal expansion coefficient higher than that of the oxide superconductor film 2.

The superconductor shown in FIG. 1 was prepared as follows. In the first step, a Y123 seed crystal 2A was formed in a thickness of about 100 to 200 nm by a pulsed laser deposition (PLD) technique on the substrate 1 consisting of YSZ having (100) plane on the surface. The seed crystal 2A was to be used as a seed in the subsequent step of depositing a Y123 film by liquid phase epitaxy (LPE). Then, 100g of $\text{YBa}_2\text{Cu}_3\text{O}_{6+x}$, 65g of BaO, 60g of CuO and 6g of BaF_2 were loaded in an yttria crucible, followed by heating the crucible in an electric furnace to 800 to 1,000°C so as to melt the materials. Under this condition, the substrate 1 was kept in contact for 10 minutes with the melt whose surface temperature was set at about 930°C while rotating the substrate 1 at

100 rpm so as to deposit a Y123 film 2B in a thickness of 2 to 10 μm on the Y123 seed crystal 2A. Further, the substrate 1 was moved away from the melt surface while keeping the substrate 1 horizontal so as to solidify the oxide material containing as a main component a Ba-Cu-O oxide, thereby forming a coating film 3 in a thickness of about 0.1 to 0.5 mm. The resultant structure was taken out of the electric furnace and cooled to room temperature.

The resistance of the resultant sample between both ends of the YSZ substrate was found to be about 10Ω supporting a relatively high electrical conductivity. This also supports that cracks did not occur in the Y123 film.

For comparison, a film structure was prepared by forming a Y123 seed crystal 2A and a Y123 film 2B on a YSZ substrate 1 but without forming a coating film. The structure was taken out of an electric furnace and cooled to room temperature. When the Y123 film 2B was observed with an optical microscope, cracks were found in the Y123 film. Further, the structure was subjected to a heat treatment at 500°C for 100 hours under a flowing oxygen for imparting a superconductivity to the Y123 film. When the Y123 film was observed with an optical microscope, innumerable cracks were found in the film supporting that cracks are increased after annealing under a flowing oxygen. Still further, according to measurement of magnetization with superconducting quantum interference device (SQUID), transition to superconducting state was found to take place in the Y123 film at 90K. However, when resistance between both ends of the YSZ substrate was measured at room temperature, current was not detected.

It has also been confirmed that, in the case of forming a coating film, cracks do not occur in the superconductor film even after annealing under a flowing oxygen.

Example 2

FIG. 2 is a cross sectional view showing the oxide superconductor prepared in this Example. As shown in the drawing, a Y123 seed crystal 2A is formed to cover a half of the circumferential surface of a fiber 11 consisting of a YSZ single crystal. Also, a Y123 film 2B is formed on three regions of the Y123 seed crystal 2A. Further, a coating film 3 is formed to cover the entire surface of the fiber 11 including these oxide superconductor films. The fiber type oxide superconductor can be applied for a superconducting wire.

The fiber type oxide superconductor was prepared as follows. In the first step, the fiber 11 about 3 cm long was prepared by cutting a YSZ single crystal fiber about 22 cm in length and about 0.30 to 0.40 mm in diameter, which was prepared by laser pedestal growth technique using a CO_2 laser. The crystal orientation of the fiber was (100) or (110).

The Y123 seed crystal 2A was formed in a thickness of about 100 to 200 nm to cover a half of the circumfer-

ential surface of the fiber 11 by a pulsed laser deposition (PLD) technique as in Example 1. On the other hand materials equal to those in Example 1 were loaded in an yttria crucible and melted by heating in an electric furnace to 800 to 1 000°C. Then a holder made of a MgO single crystal and horizontally holding the fiber 11 at both ends of the fiber 11 was mounted to a lower end of a rotary shaft. Under this condition the fiber 11 was brought into contact with the melt so as to permit growth of the Y123 film 2B on the Y123 seed crystal 2A while rotating the fiber 11 within a horizontal plane. In this step the Y123 film 2B having a width of 50 to 100 µm and a thickness of 10 to 20 µm was found to grow on three regions of the Y123 seed crystal 2A. Then the fiber 11 was moved upward away from the melt surface such that the fiber 11 was kept horizontal so as to allow the melt of the Ba-Cu-O based oxide to be solidified thereby forming a coating film 3 having a thickness of about 100 to 200 µm and covering the entire surface of the fiber 11.

It should be noted that, if the fiber 11 is moved up slightly the melt surface is upheaved by the surface tension of the melt so as to permit the melt to be kept in contact with the fiber. The upheaved portion of the melt is cooled to temperatures somewhat lower than the melting point of the melt. It follows that a temperature gradient is imparted to the upheaved portion of the melt in accordance with the height of the upheaval. In order to make the coating film 3 satisfactory, the fiber 11 is moved away from the melt surface such that the fiber 11 is kept in contact with the upheaved portion of the melt for 20 seconds to 2 minutes. During the procedure the fiber temperature falls within a range between a level immediately below the melting point and 50°C below the melting point of the melt. Also it is desirable for the coating film 3 to have a thickness of at least 10 µm. If the thickness of the coating film 3 is less than 10 µm which is substantially equal to or thinner than the oxide superconductor film, the coating film 3 fails to produce the effect of suppressing the crack occurrence in the oxide superconductor film. On the other hand, it is very difficult to form uniformly a coating film having a thickness exceeding 300 µm on the fiber surface.

The resistance of the resultant sample was found to be zero in the vicinity of 90K. Also, the critical current under the liquid nitrogen temperature was found to be about 1A.

FIG. 3 is a graph showing the relationship between the magnetic field and the critical current of the resultant Y123 film. As seen from the graph, the critical current is gradually decreased with increase in the magnetic field. This supports that a weak link is not produced between the superconducting grains, and that cracks do not occur in the Y123 film.

For comparison, a film structure was prepared by forming a Y123 film on a YSZ fiber, but without forming a coating film on the Y123 film. FIG. 4 is a graph showing the relationship between the temperature and the resistance of the resultant Y123 film. As shown in the graph,

dropping of resistance accompanying the transition into a superconducting state is recognized in the vicinity of 90K. However, the Y123 film was found to exhibit a resistance of about 1Ω even at the boiling point of liquid nitrogen, and thus the critical current was zero. These experimental data are considered to support the crack occurrence in the Y123 film.

Claims

1. An oxide superconductor characterized by comprising

a base material (1-11) consisting of a single crystalline oxide

an oxide superconductor film (2B) formed on said single crystalline oxide base material (1-11); and

a coating film (3) covering the surface of said oxide superconductor film (2B), said coating film (3) having a thermal expansion coefficient higher than that of the oxide superconductor film (2B)

2. The oxide superconductor according to claim 1 characterized in that said coating film (3) consists of an oxide

3. The oxide superconductor according to claim 2 characterized in that said coating film (3) consists of an oxide containing a Ba-Cu-O oxide as a main component

4. The oxide superconductor according to claim 1 characterized in that said oxide superconductor film (2B) consists of a 1-2-3 compound represented by the general formula given below



where RE denotes at least one element selected from the group consisting of Y and rare earth elements, and $0 \leq x \leq 1$

5. The oxide superconductor according to claim 1 characterized in that said base material (1-11) consists of yttria-stabilized zirconia or SrTiO_3

6. The oxide superconductor according to claim 1, characterized in that said base material (11) is in the form of a fiber

7. A method of manufacturing an oxide superconductor, characterized by comprising the steps of:

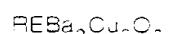
forming an oxide superconductor film (2B) by a

liquid phase growing method on a base material (1-11) consisting of a single crystalline oxide and
forming a coating film (3) by a melt solidifying
method to cover the surface of the oxide super-
conductor film (2B)

8. The method according to claim 7 characterized in
that

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said oxide superconductor film (2B) consists of
a 1-2-3 compound represented by the general
formula given below



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where RE denotes at least one element selected
from the group consisting of Y and rare earth
elements and $0 < x < 1$ and

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said coating film (3) consists of an oxide con-
taining a Ba-Cu-O oxide as a main component

9. The method according to claim 7 characterized in
that said base material (11) is in the form of a fiber

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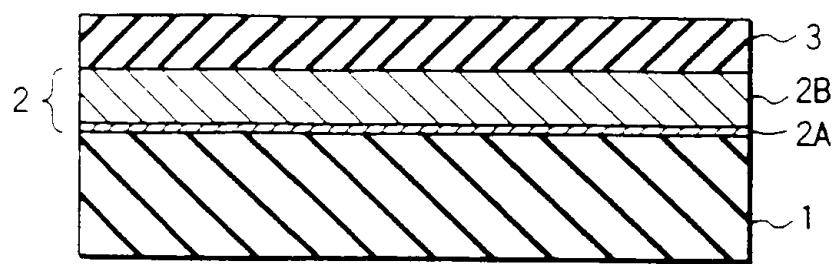


FIG. 1

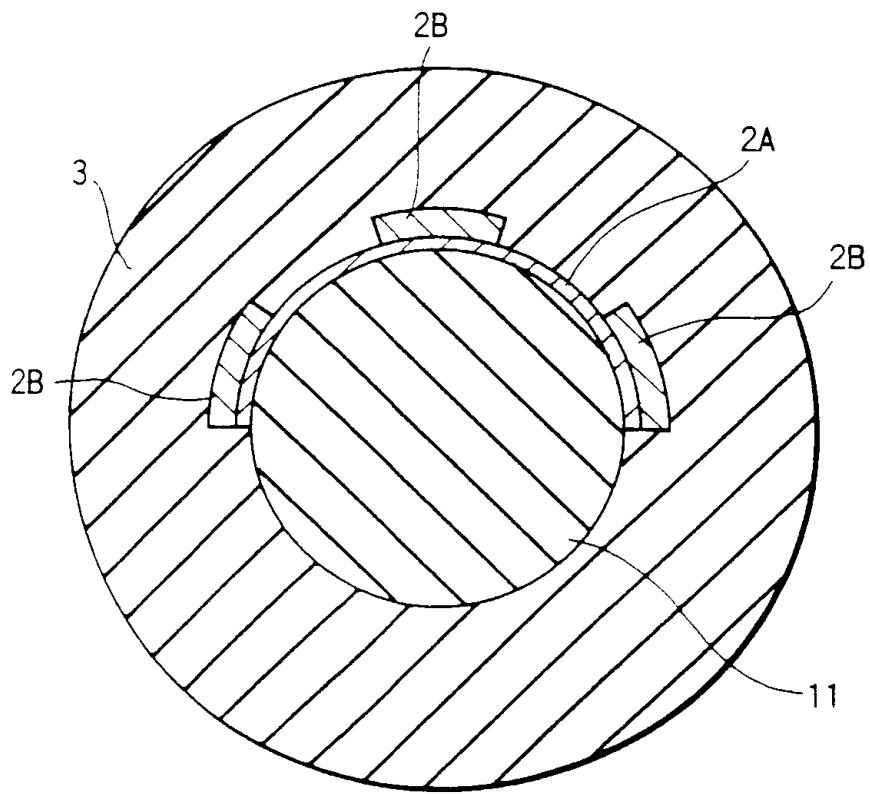


FIG. 2

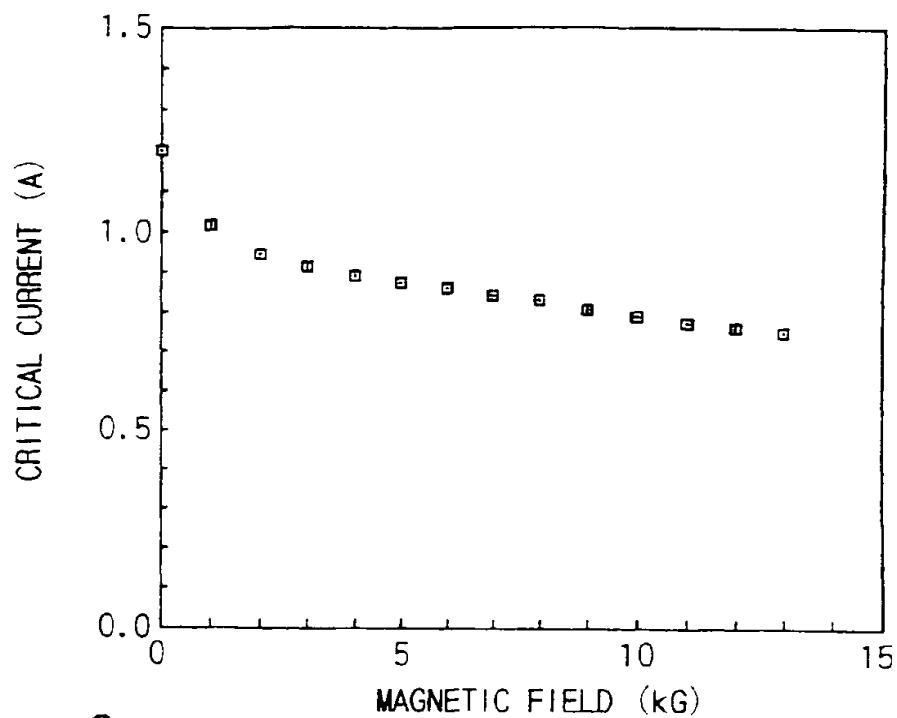


FIG. 3

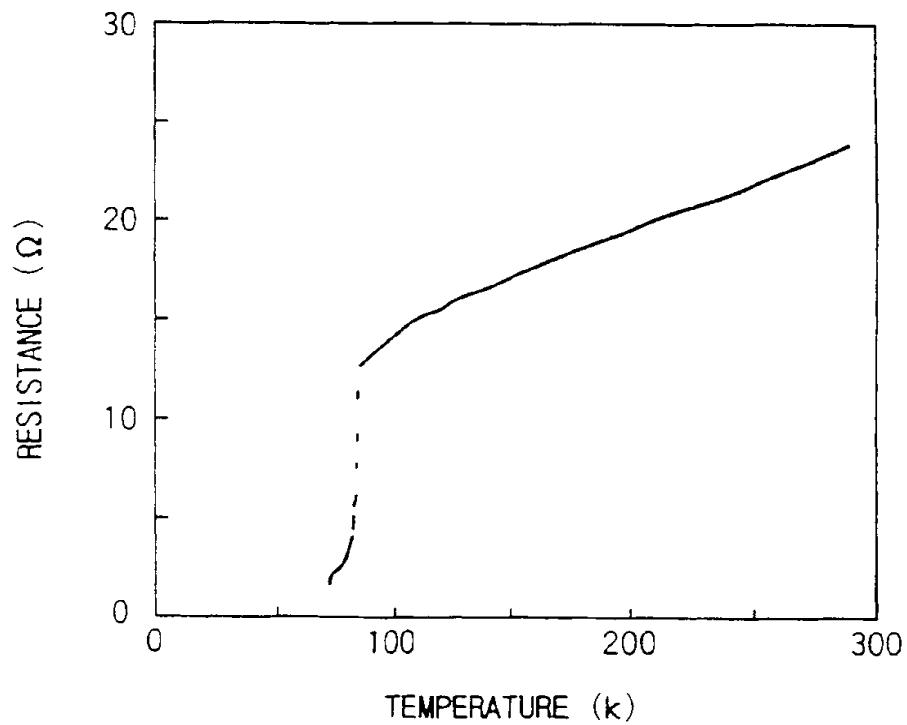


FIG. 4



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EUROPEAN SEARCH REPORT

Application Number:

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DOCUMENTS CONSIDERED TO BE RELEVANT

SEARCHED		REF ID:	CLASSIFICATION OF THE APPLICATION (Int.C.G.)
A	EP 0 440 791 A (MITSUBISHI METAL CORP.) * column 4, line 40-59 *	1	H01L39/24
✓	PATENT ABSTRACTS OF JAPAN vol. 395, no. 002, 31 March 1995 & JP 06 321694 A (KOKUSAI SHODENDO SANGYO GIJUTSU KENKYU CENTER) OTHERS, 03/11/22 November 1994. * abstract *	1,3	
✓	EP 0 334 352 A (MITSUBISHI METAL CORP.) * abstract *	1,3	
✓	EP 0 299 879 A (SUMITOMO ELECTRIC INDUSTRIES) * abstract *	1	
✓	US 5 411 938 A (WU WEITE ET AL.) * abstract *	1	
A	EP 0 561 617 A (NGK INSULATORS LTD) * page 3, line 39-46 * * page 5, line 33-36 *	1	
TECHNICAL FIELDS SEARCHED (Int.Cl.6)			401L

**TECHNICAL FIELDS
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The present search regimen has been designed to identify all cases.

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SEARCH OF CITED DOCUMENTS

- 1. **Plaintiff's relevant tax-exempt organization, any relevant organization which documents the same date period.**
- 2. **Plaintiff's principal group, any relevant organization which documents the same date period.**
- 3. **Plaintiff's subscriber, any relevant organization which documents the same date period.**

- 7. **Parental guidance during the initiation**
Learning the language can be described as:
 - a) the first rule
 - b) the first app which
 - c) the first book of their reading
- 8. **Parents of the same parent arrive - Unquestioning**
parents